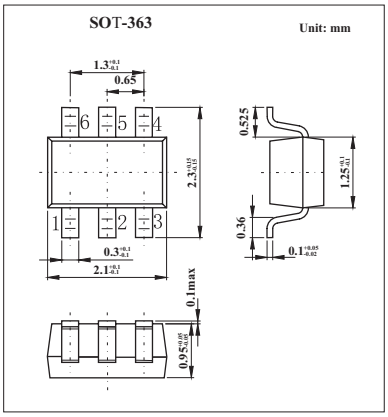
Schottky Barrier Double Diode

BAT74S



Features

- Low forward voltage
- Guard ring protected
- Small SMD package.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Per diode					
continuous reverse voltage	V_R			30	V
continuous forward current	I_F			200	mA
repetitive peak forward current	I_{FRM}	$t_p \leqslant 1$ s; $\delta \leqslant 0.5$		300	mA
non-repetitive peak forward current	I_{FSM}	$t_p < 10$ ms		600	mA
storage temperature	T_{stg}		-65	+150	℃
junction temperature	T_j			125	℃
operating ambient temperature	T_{amb}		-65	+125	℃
Double diode operation					
continuous reverse voltage	V_R			30	V
continuous reverse voltage	V_R	series connection		60	V
continuous forward current	I_F			110(1)	mA
repetitive peak forward current	I_{FRM}	$t_p \leqslant 1$ s; $\delta \leqslant 0.5$		200	mA
thermal resistance from junction to ambient	$R_{th\ j\text{-}a}$			416	K/W

Note

1. If both diodes are in forward operation at the same moment, total device current is max. 110 mA.

If one diode is in reverse and the other in forward operation at the same moment, total device current is max. 200 mA.

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Max	Unit
forward voltage	V_F	I_F = 0.1 mA	200	mV
		I_F = 1 mA	260	
		I_F = 10 mA	340	
		I_F = 30 mA	420	
		I_F = 100 mA	750	
reverse current	I_R	V_R = 25 V; note 1	2	μA
reverse recovery time	t_{rr}	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ;measured at I_R = 1 mA	5	ns
diode capacitance	C_d	f = 1 MHz; V_R = 1 V	10	pF

Note

1. Pulse test: tp = 300 μs; δ = 0.02.

■ Marking

Marking	74